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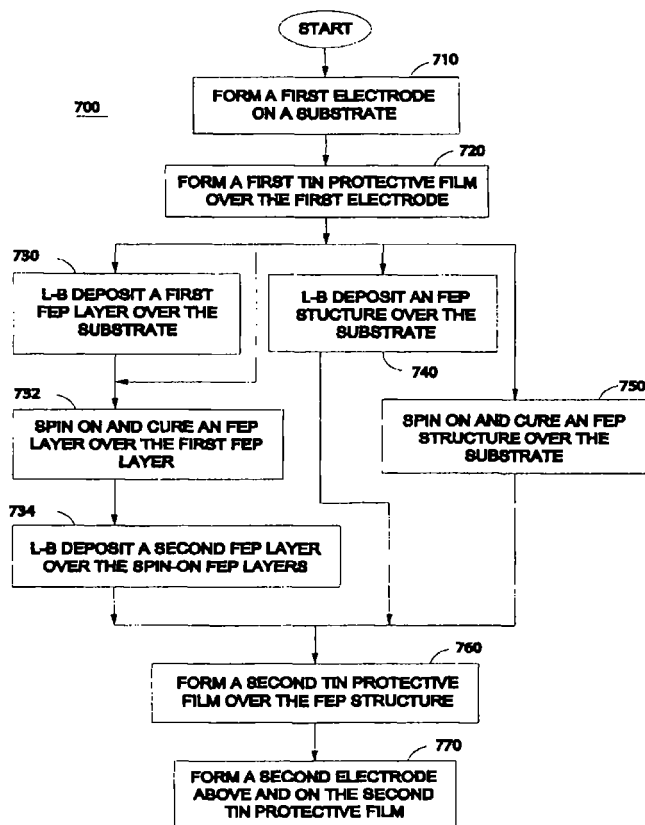
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- (71) Applicant: **INTEL CORPORATION** [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US).
- (72) Inventors: **ISENBERGER, Mark**; 78 Dulce Court, Corrales, NM 87048 (US). **MU, Xiao-Chun**; 19685 Via Escuela Drive, Saratoga, CA 95070 (US). **LI, Jian**; 1008 Live Oak Terrace, Sunnyvale, CA 94086 (US).
- (74) Agents: **MALLIE, Michael, J.** et al.; Blakely Sokoloff Taylor & Zafman, 12400 Wilshire Boulevard, 7th Floor, Los Angeles, CA 90025 (US).
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(54) Title: LOW-VOLTAGE AND INTERFACE DAMAGE-FREE POLYMER MEMORY DEVICE



(57) Abstract: One embodiment of the invention relates to a polymer memory device and a method of making it. The polymer memory device may include a composite or single layer of a ferroelectric polymer memory that addresses surface engineering needs according to various embodiments. The ferroelectric polymer memory structure may include crystalline ferroelectric polymer layers such as single and co-polymer compositions. The structure may include spin-on and/or Langmuir-Blodgett deposited compositions. One embodiment of the invention relates to a method making embodiments of the polymer memory device. One embodiment of the invention relates to a memory system that allows the polymer memory device to interface with various existing hosts.



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